WNSC5D10650T



Silicon Carbide Diode

Rev.01 - 10 October 2022

Product data sheet

1. General description

Silicon Carbide Schottky diode in a DFN 8*8 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
V_{RRM}	V _{RRM} repetitive peak reverse 650 voltage					V	
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _c ≤ 149 °C; Fig. 1; Fig. 2; Fig. 3		10		А	
Tj	junction temperature			-55 to 175		°C	
Symbol	Parameter	Conditions	Notes	Min Typ Max		Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.45	1.70	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.80	2.20	V
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 10 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	14.5	-	nC

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[]	к . К. А
2	n.c.	not connected	5	001aaa020
3	A	anode		
4	А	anode		
5	К	mounting base; connected to cathode	1 2 3 4	

6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	name		method	quantity	version	issue date		
WNSC5D10650T	DFN8*8	WNSC5D10650T6J	Таре	3000	DFN8X8N	25-Dec-2019		

7. Marking

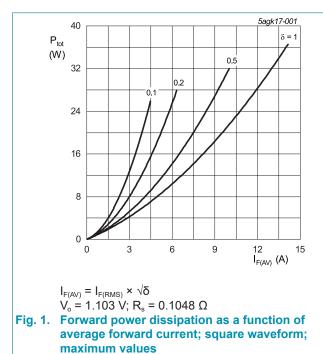
Та	Table 4. Marking codes						
	Гуре number	Marking codes					
١	WNSC5D10650T	WNSC5D					
		10650T					

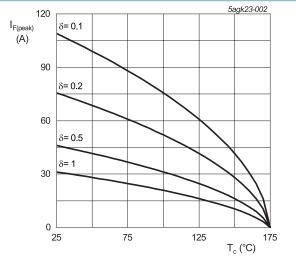
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

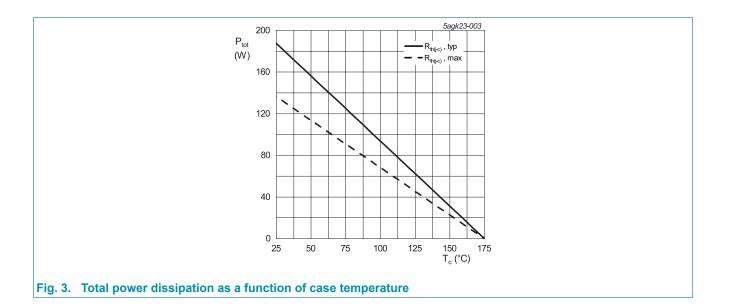
Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _c ≤ 149 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _c ≤ 149 °C; square-wave pulse		20	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		50	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse		540	А
l ² t	I ² t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms		18	A ² s
T _{stg}	storage temperature			-55 to 175	°C
T _j	junction temperature			-55 to 175	°C





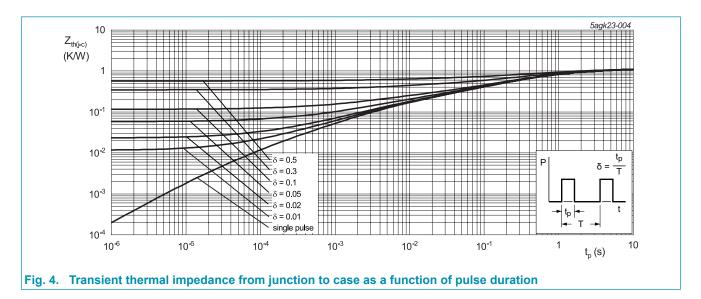


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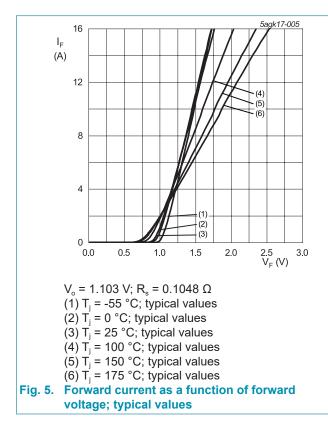
9. Thermal characteristics

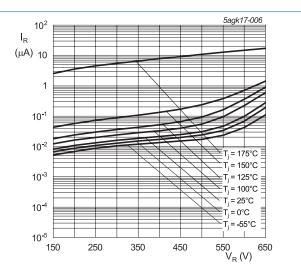
Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	<u>Fig. 4</u>		-	0.8	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	50	-	K/W



10. Characteristics

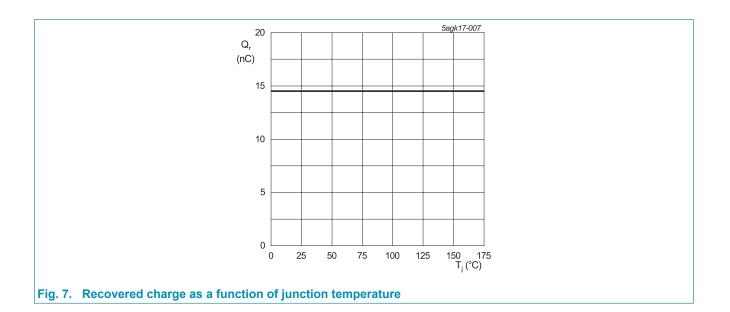
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V _F	forward current	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.45	1.70	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.80	2.20	V
		I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u>		-	2.00	2.30	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>		-	0.5	50	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>		-	25	250	μA
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	14.5	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	323	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	38	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	35	-	pF
E _{as}	non-repetitive avalanche energy	$I_R = 4.9 \text{ A}; \text{ L} = 5 \text{ mH}; \text{ T}_{j(init)} = 25 \text{ °C}$		60	-	-	mJ



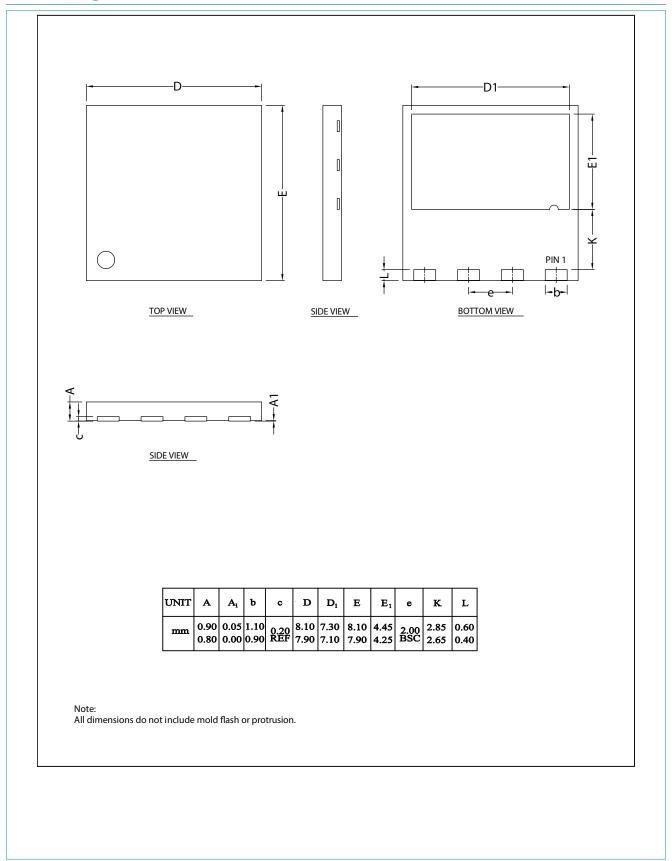




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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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